

Sub-200 fs-MIXSEL

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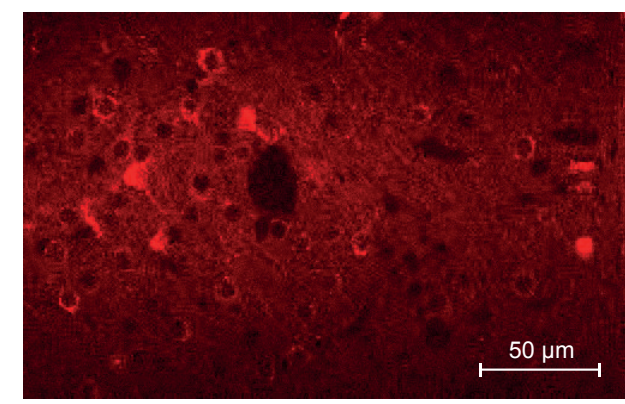
Eidgenössische Technische Hochschule Zürich
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Motivation

Potential applications of ultrafast semiconductor disk lasers (SDL)



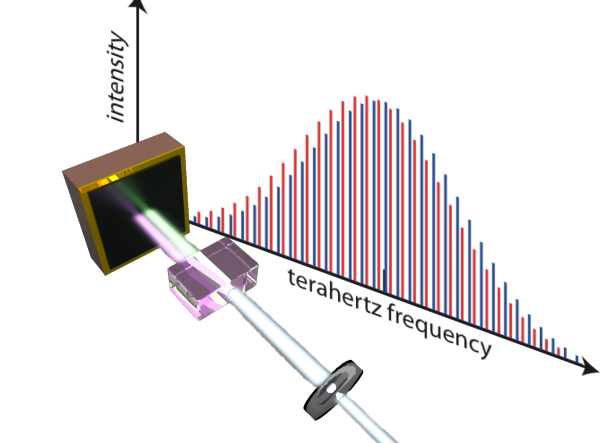
metrology



biomedical imaging



natural user interface



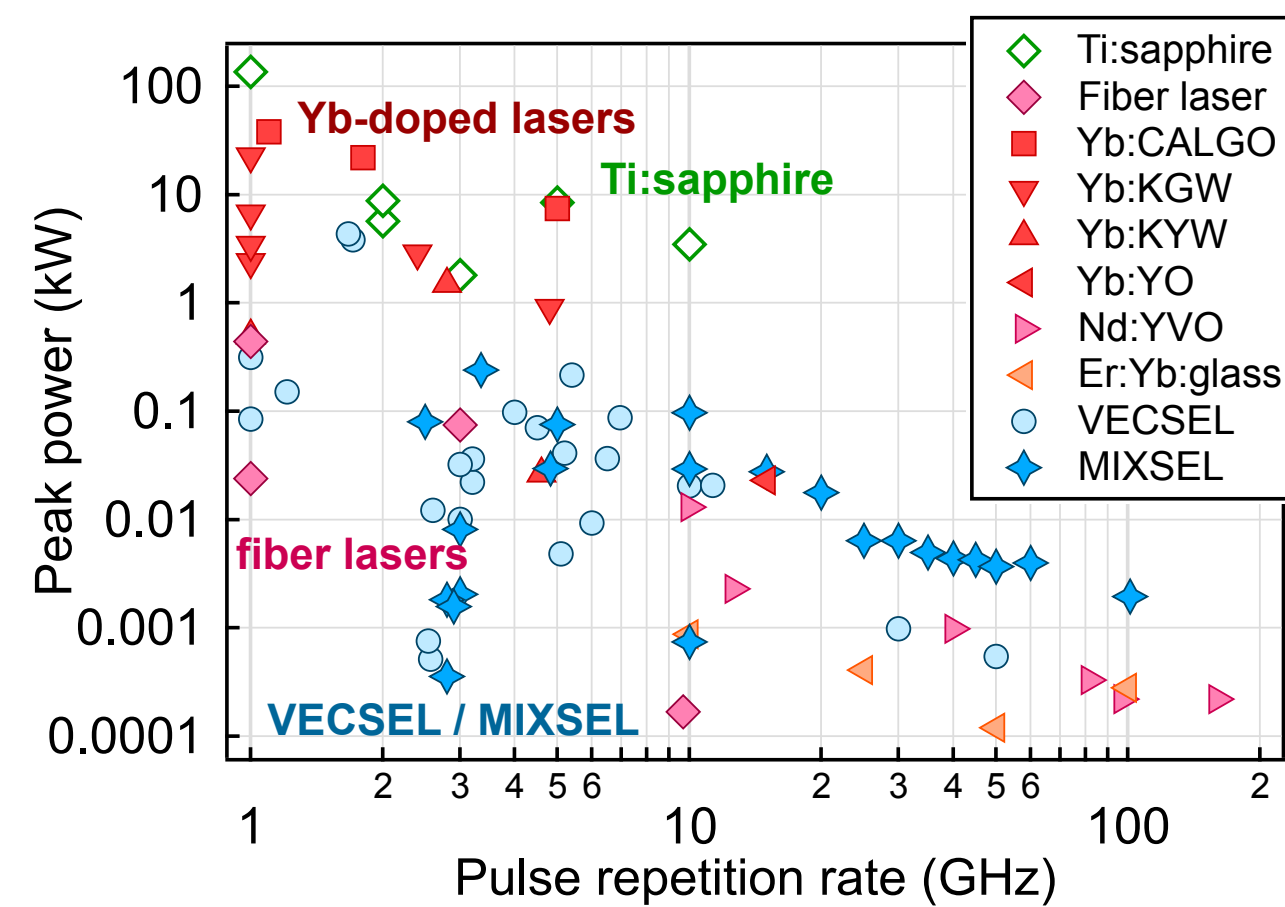
spectroscopy and frequency combs

first CEO-frequency detection of a SESAM-modelocked VECSEL [1]

amplified and recompressed 238-fs pulses from a 100-mW VECSEL

Enabling key technology for applications at 1-100 GHz repetition rate

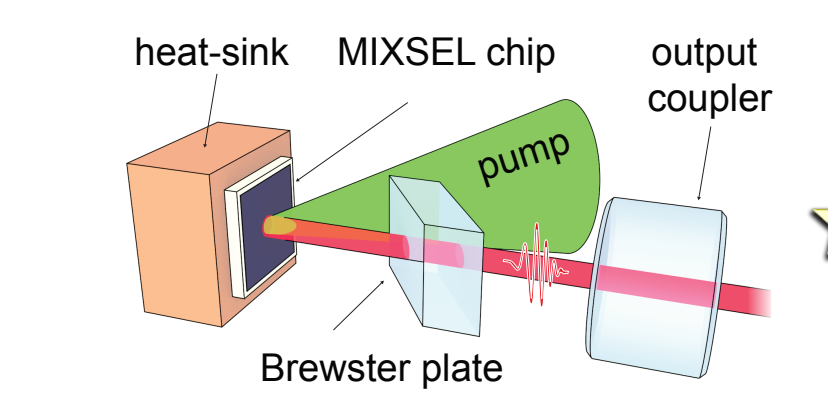
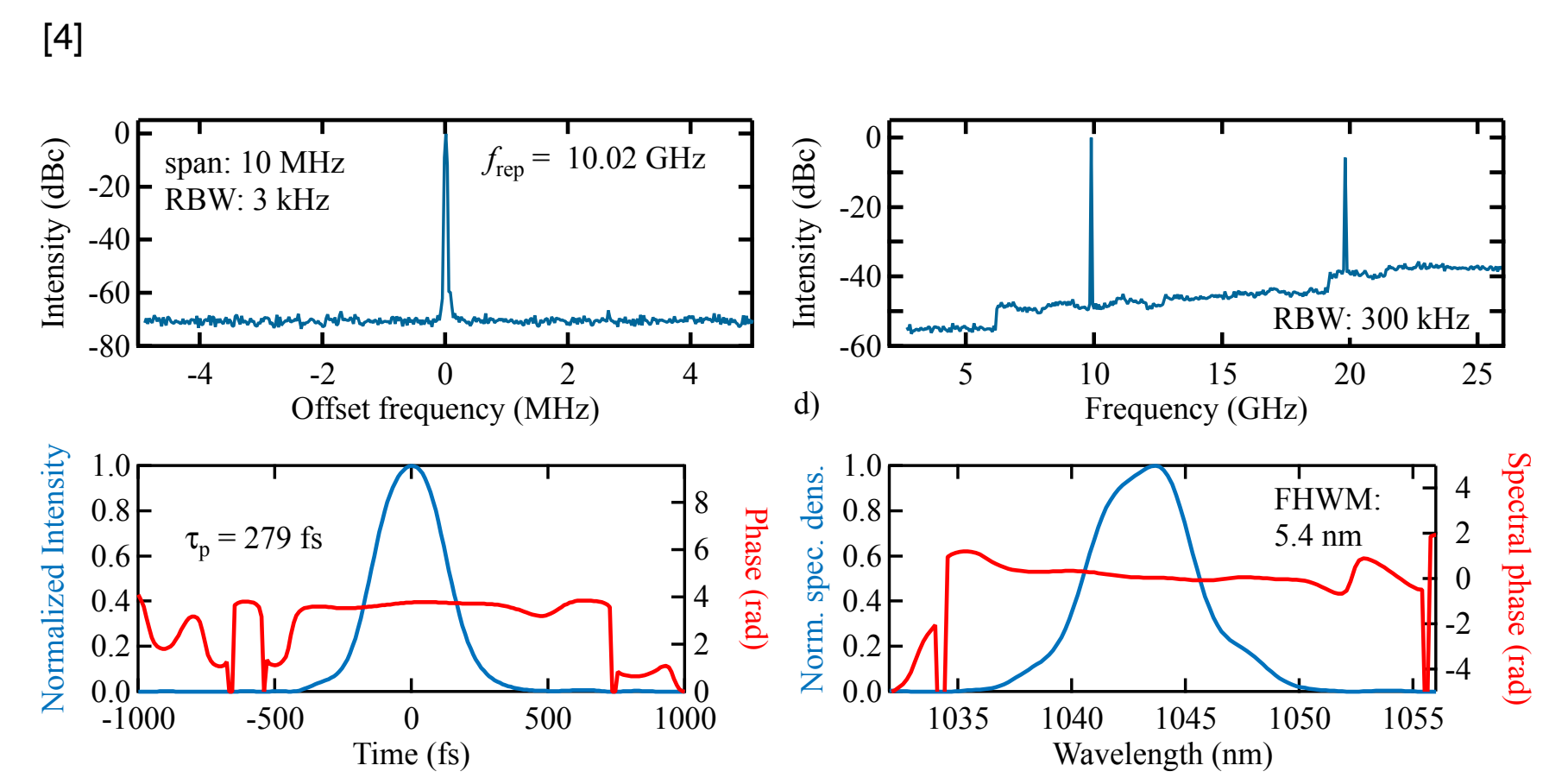
[1] C.A. Zaugg et al., Optics Express (2014) Vol. 22, 16445-16455



Recent results

Pulse duration: **279 fs**
Average output power: **310 mW**
Opt. to opt. efficiency: **1.34%**
Repetition rate: **10 GHz**
Center wavelength: **1043 nm**

• Highest average power of fs-MIXSEL
• High peak power:
 $P_{peak} = 97 \text{ W}$



Sub-200-fs MIXSEL

Pulse duration: **184 fs**
Average output power: **115 mW**
Opt. to opt. efficiency: **0.7%**
Repetition rate: **4.33 GHz**
Center wavelength: **1048 nm**

• Shortest pulse duration of a MIXSEL
• High peak power:
 $P_{peak} = 130 \text{ W}$

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Average output power: **115 mW**
Opt. to opt. efficiency: **0.7%**
Repetition rate: **4.33 GHz**
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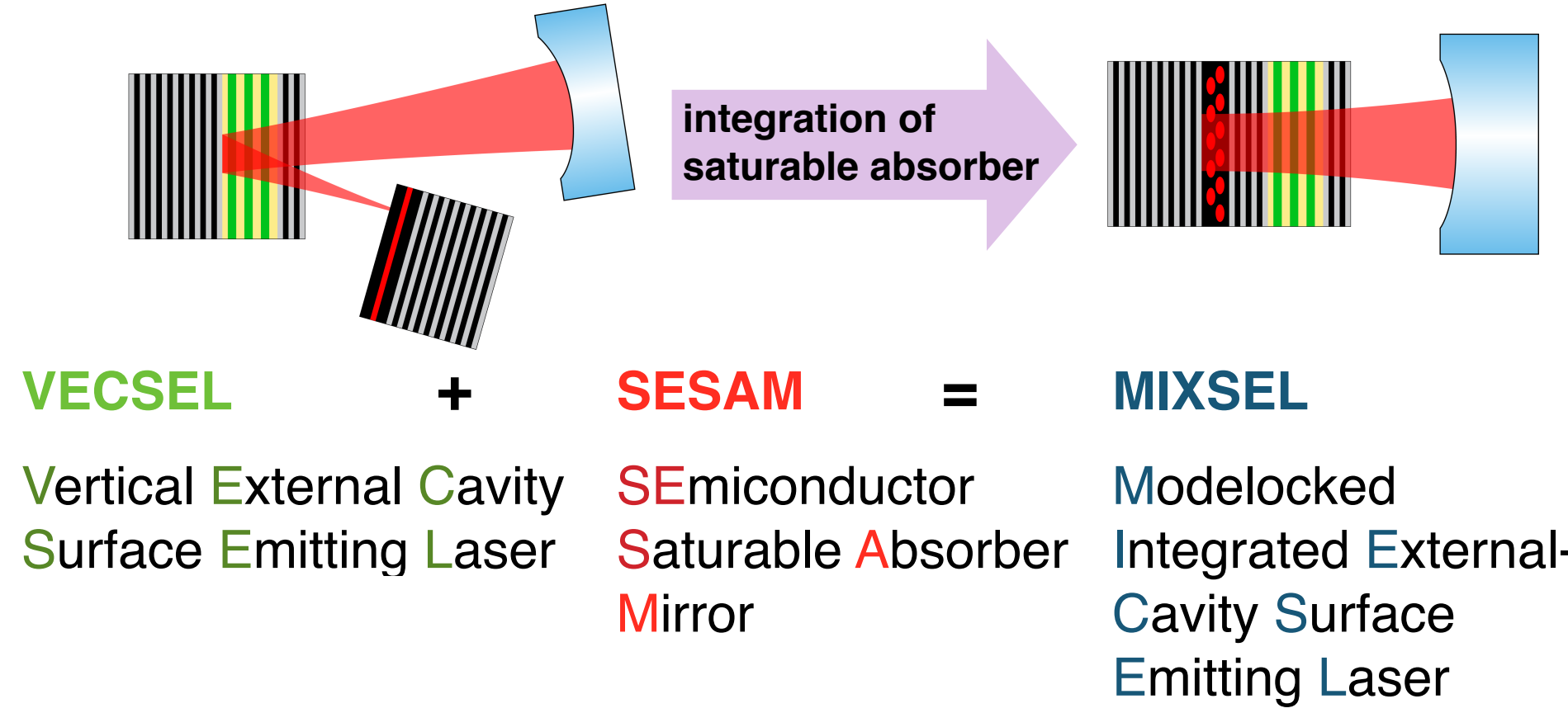
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• Shortest pulse duration of a MIXSEL
• High peak power:
 $P_{peak} = 130 \text{ W}$

[4] M. Mangold et al., Optics Express (2015) Vol. 23, 22043-22059

MIXSEL concept

- Semiconductor based
- Integrated saturable absorber
- Potential for monolithic design
- Low noise operation
- Straight cavity for simplified repetition rate scalability



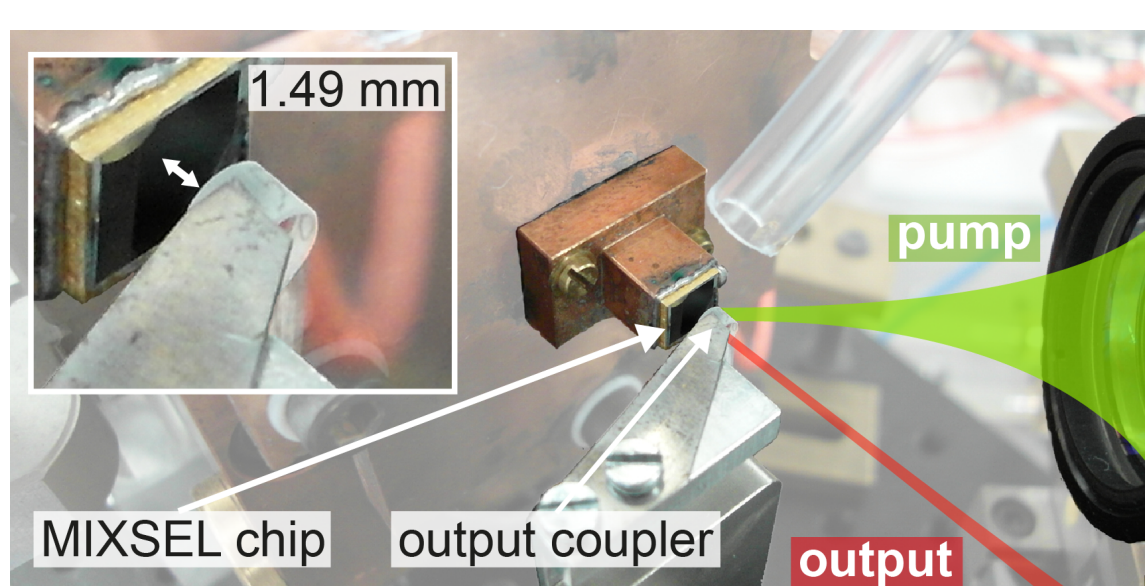
modelocking results

28.1 ps pulse duration, 6.4 W output power, 2.5 GHz repetition rate

• Highest output power of a modelocked semiconductor laser [2]

230 fs pulse duration, 132 mW output power, 3.9 GHz repetition rate

• Shortest pulse duration from a MIXSEL



• Femtosecond operation at 100 GHz: highest repetition rate of any fundamental mode locked SDL [3]

[2] B. Rudin, et al., Opt. Exp. (2010) vol. 18, pp. 27582
[3] M. Mangold et al., Optics Express, vol. 22, No. 5, pp. 6099-6107, 2014

MOVPE MIXSEL

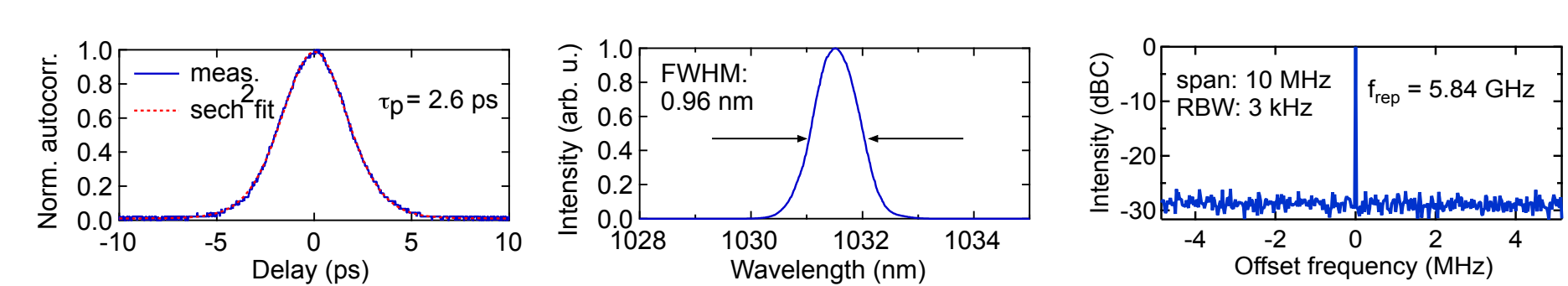
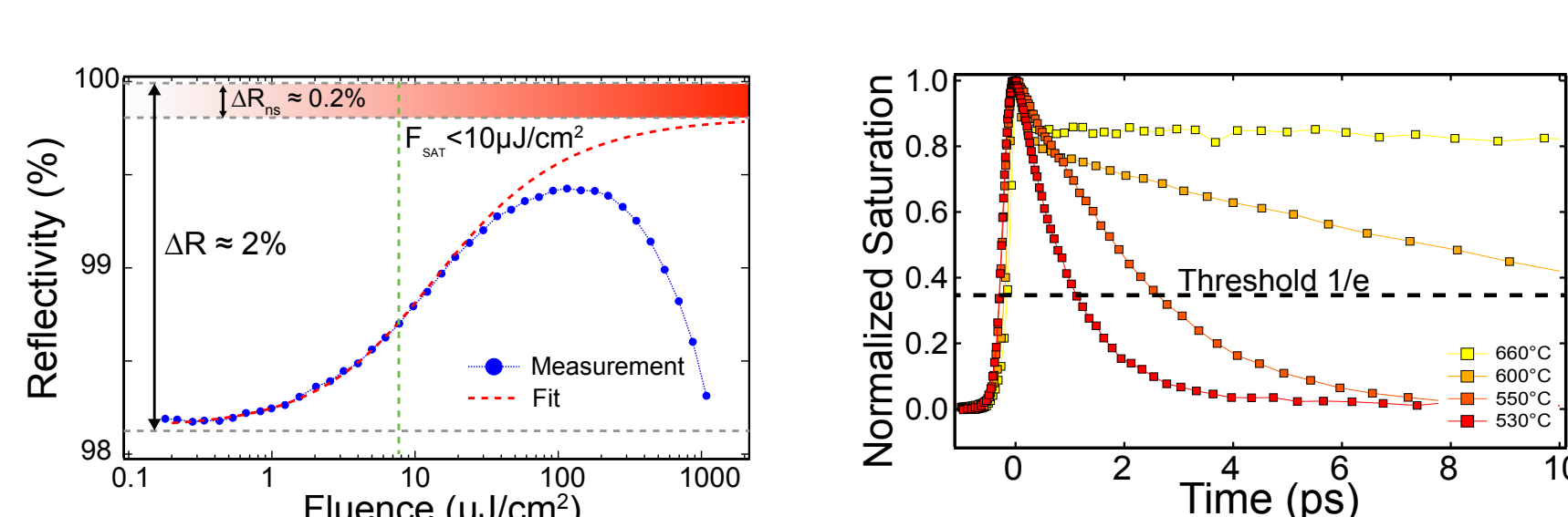
- Easier access to strain compensation
- More uniform structure for better performances
- Industry-oriented large scale MIXSEL production

Need to optimize low temperature grown saturable absorbers from MOVPE

MOVPE absorber characterisation

- Low saturation fluence ($< 5 \mu\text{J}/\text{cm}^2$)
- Low non saturable losses ($< 0.4\%$)
- Fast recovery time ($< 5 \text{ ps}$)

Single quantum-well (QW) absorber

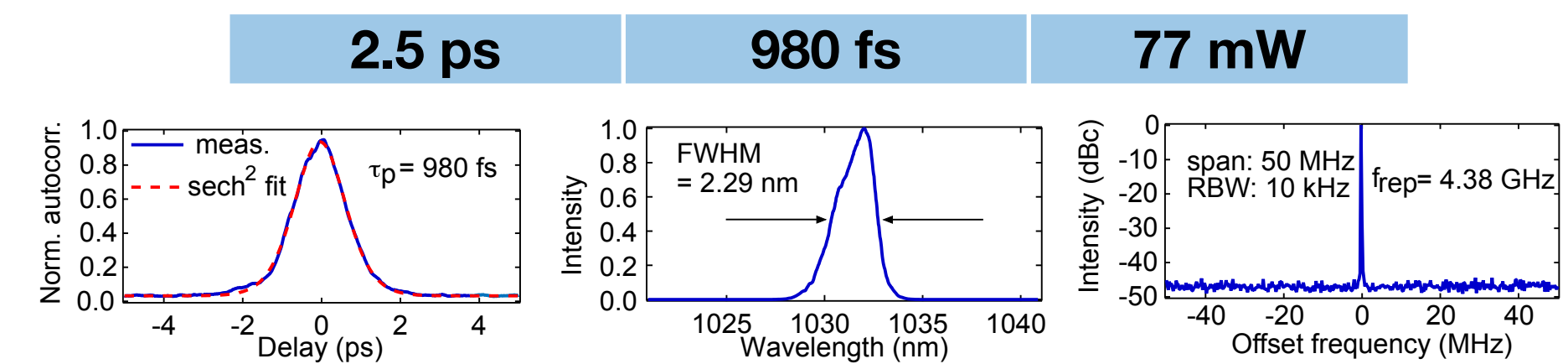


We demonstrated the first generation of MOVPE MIXSELS:

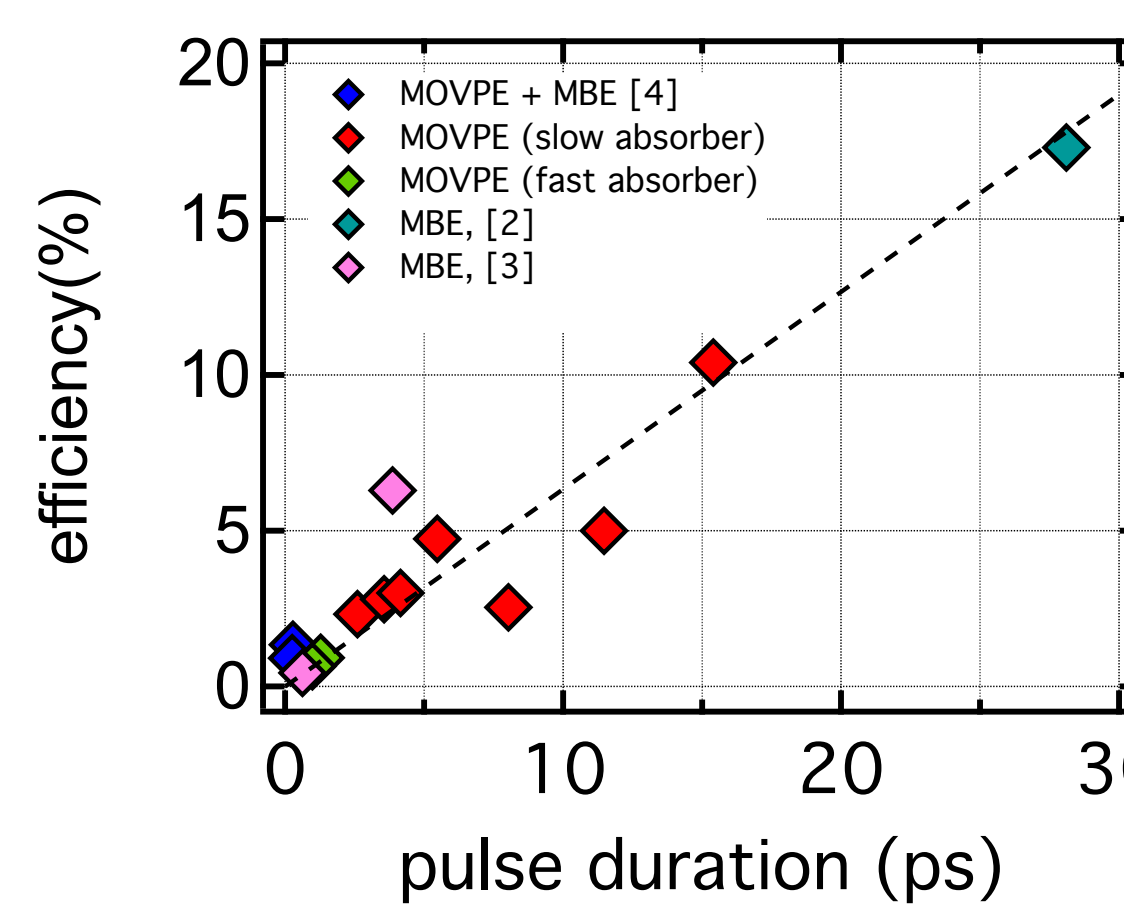
• Pulse duration was shortened by a faster absorber.

• At this point still a trade-off between faster absorber and low non-saturable losses.

• Lower F_{sat} will allow sub-300-fs operation from MOVPE MIXSELS



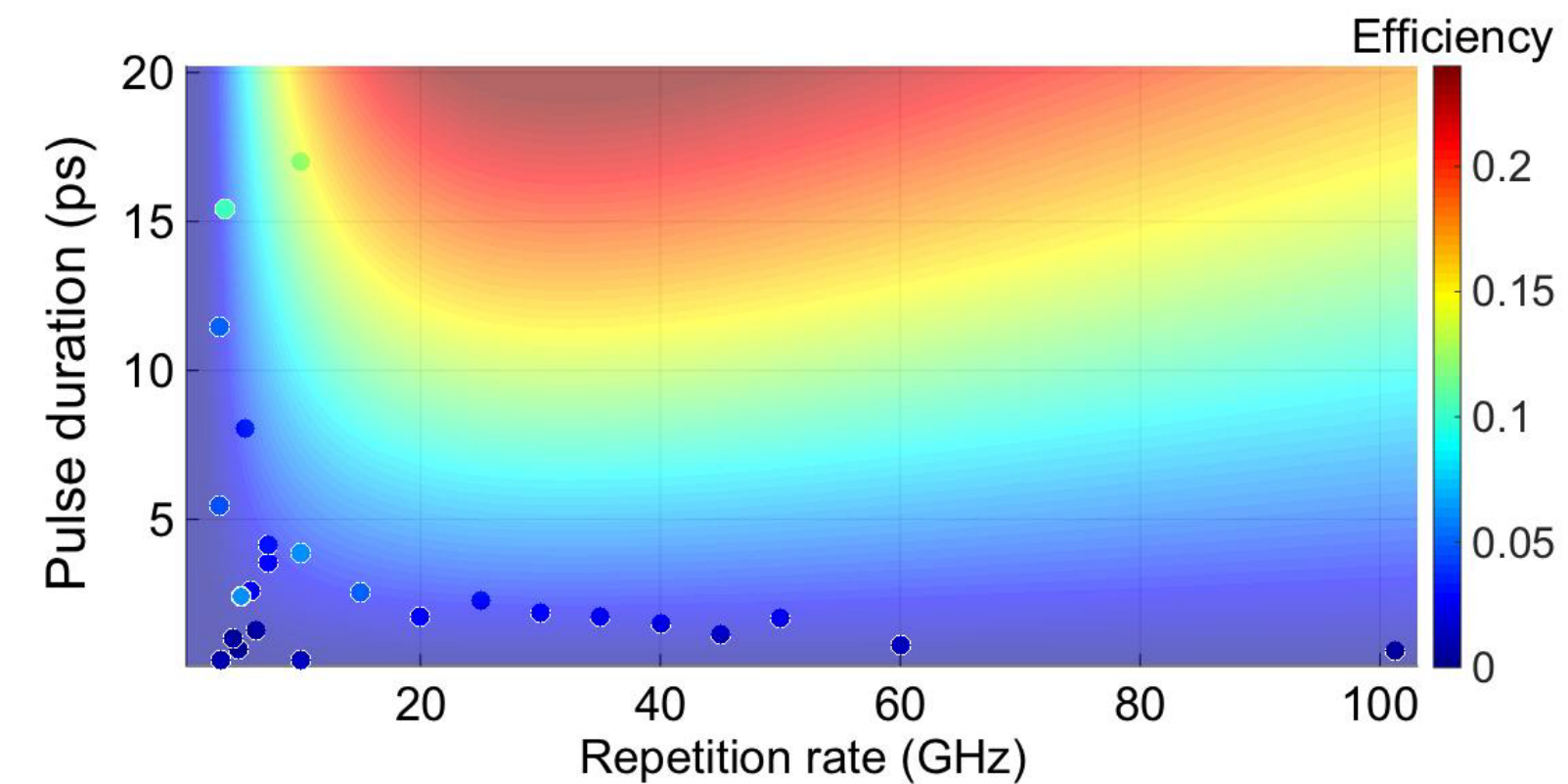
Challenges for performance scaling



• Increase the optical-to-optical efficiency in fs-operation

Carriers pumped into the gain QWs create a reservoir. A fs-pulse is not using all the carriers for stimulated emission. The remaining part decays spontaneously affecting the efficiency.

- For fs-MIXSELS the efficiency is typically $\approx 1\%$
- Repetition rate has an influence on the efficiency



MIXSEL data points fitted to a model for efficiency simulation

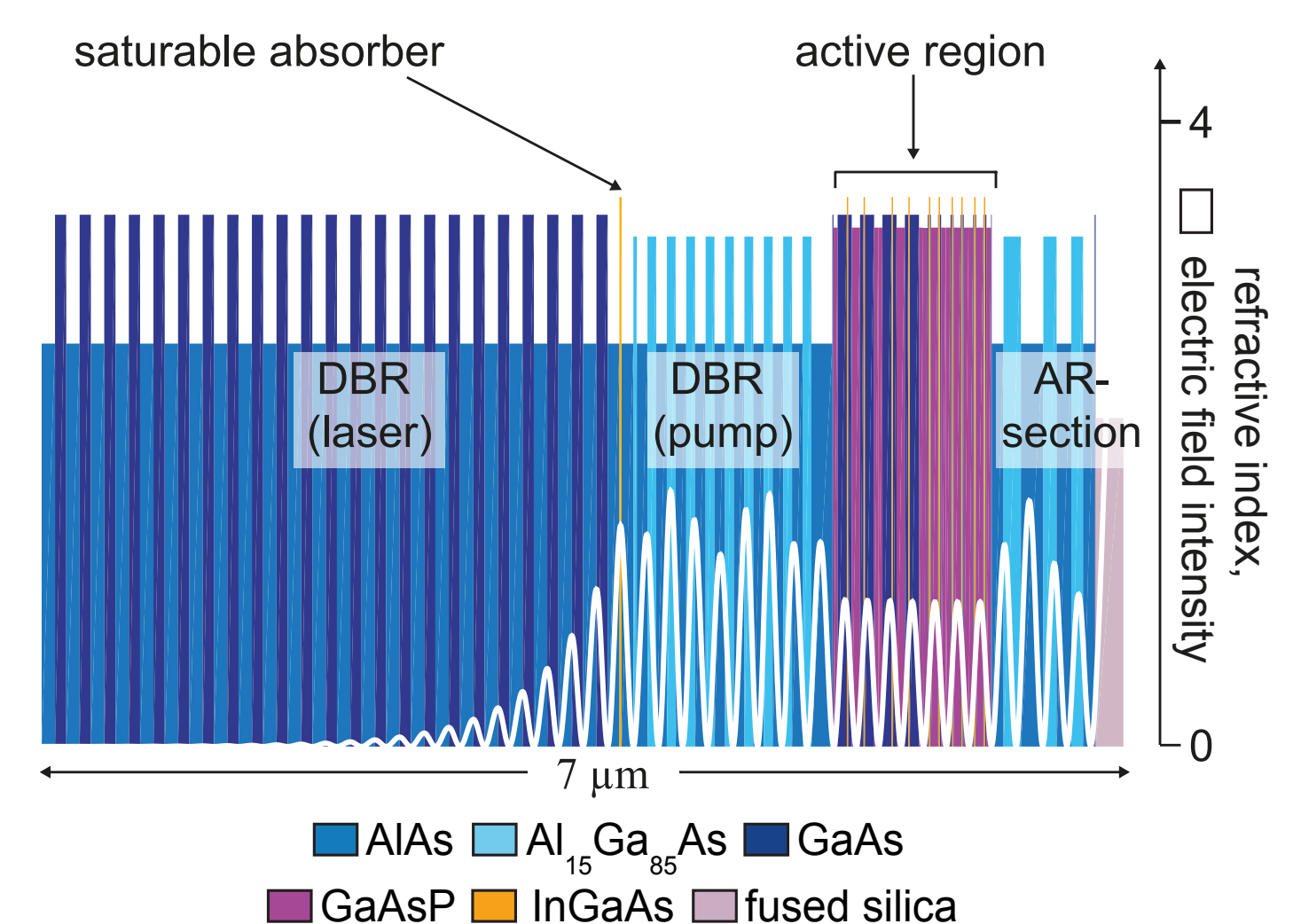
To enhance the efficiency:

- Increase the carrier lifetime in the gain QWs
- Use quantum dots with longer life times as gain medium
- Bandgap engineering

• Reduce losses induced by two-photon absorption (TPA)

At high power two photon absorption (TPA) becomes stronger and transparent layers become absorptive

- TPA prevents further power scaling
- TPA losses are higher at short pulse duration

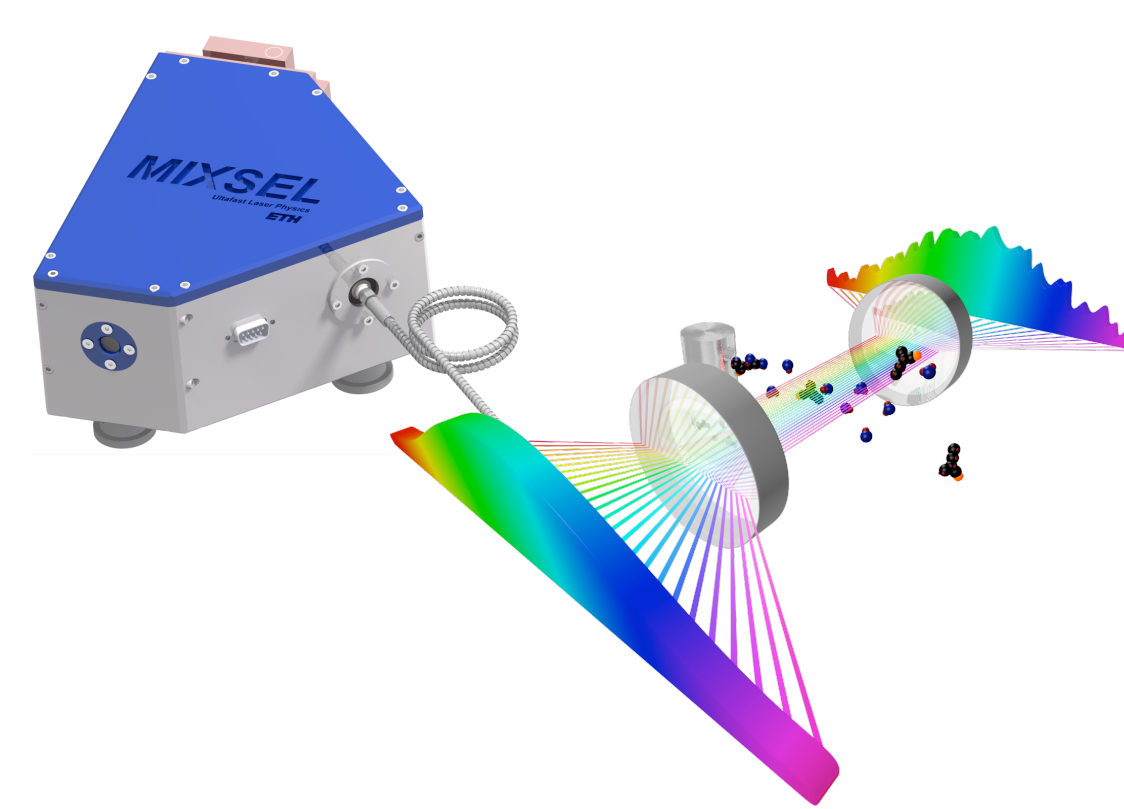


• Where the electric field is more intense (i.e. pump DBR, AR section) TPA is increased

• Low bandgap materials (i.e. GaAs, GaAsP, Al₁₅Ga₈₅As) contribute more to TPA

- Design full dielectric AR section and reduce the electric field in the pump DBR
- Use large bandgap materials (i.e. AlAsP) for strain compensation instead of GaAsP

Outlook



next steps: sub-200-fs pulses with $> 1 \text{ kW}$ peak power from a MIXSEL

ultimate goal: fully stabilized frequency comb (repetition rate & CEO-frequency) from a compact, low cost MIXSEL